

November 2017

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30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) max	I _D T _A = +25°C
-30V	$95m\Omega @ V_{GS} = -10V$	-2.5A
-30 V	145mΩ @ $V_{GS} = -4.5V$	-2.0A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- **Boost Switch**
- **Power Management Functions**
- Analog Switch
- Load Switch

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

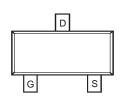
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

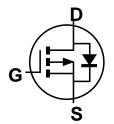




Top View



SOT23



Equivalent Circuit

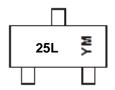
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3125L-7	SOT23	3,000/Tape & Reel
DMP3125L-13	SOT23	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



25L = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	20	019	2020	2021		2	2022	2023	202	24	2025
Code	Е	F		G	Н				J	K	L	-	M
Month	Jan	Feb	Mar	Apr	May	Jun	Jı	ul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	7	8	9	0	N	D

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Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	I _D	-2.5 -2.0	А
Maximum Continuous Body Diode Forward Current (Is	-1.5	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-10	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	0.65	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	191	°C/W
Total Power Dissipation (Note 6)		P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	103	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

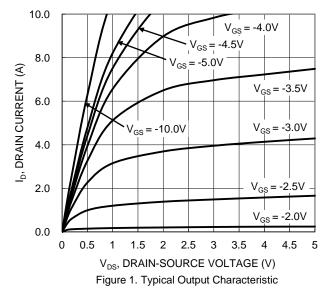
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}			-1	μA	V _{DS} = -30V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0		-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	7		76	95	mΩ	$V_{GS} = -10V, I_D = -3.8A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	108	145	mu	$V_{GS} = -4.5V, I_D = -3.0A$	
Diode Forward Voltage	V _{SD}		-0.85	-1.2	V	$V_{GS} = 0V, I_S = -2.7A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	1	254	-	pF		
Output Capacitance	Coss	_	14	_	pF	$V_{DS} = -25V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	7	_	pF	1 - 1.000112	
Gate Resistance	R_g	_	54	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	Q_g	_	3.1	_	nC		
Gate-Source Charge	Q _{gs}	_	0.8	_	nC	$V_{GS} = -4.5V, V_{DS} = -15V$ $I_{D} = -3.8A$	
Gate-Drain Charge	Q _{gd}	_	1.4	_	nC	1D = -3.6A	
Turn-On Delay Time	t _{D(ON)}	_	3.5	_	ns		
Turn-On Rise Time	t _R		6.3	_	ns	V _{DS} = -15V, V _{GS} = -10V,	
Turn-Off Delay Time	t _{D(OFF)}	_	21.8	_	ns	$R_G = 6.0\Omega, I_D = -1A$	
Turn-Off Fall Time	t _F	_	13.1	_	ns		
Reverse Recovery Time	t _{RR}	_	9.6	_	ns	I _F = -1.0A, di/dt = 100A/μs	
Reverse Recovery Charge	Q _{RR}	_	2.4		nC	I _F = -1.0A, di/dt = 100A/μs	

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

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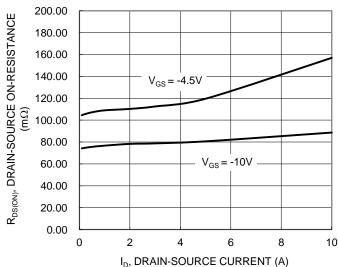
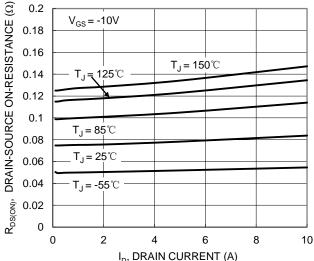
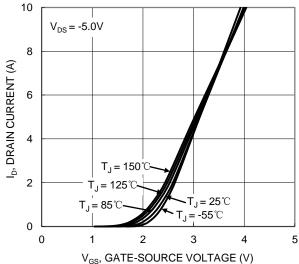


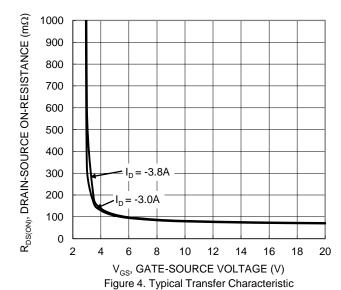
Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage



I_D, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs. Drain Current and Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V)
Figure 2. Typical Transfer Characteristic



2 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 1.8 1.6 $V_{GS} = -10V, I_{D} = -3.8A$ 1.4 1.2 1 -4.5V, $I_D = -3.0A$ 0.8 0.6 0.4 -25 0 25 50 75 100 125 150 -50

 $\mathsf{T_J},\mathsf{JUNCTION}$ TEMPERATURE (°C) Figure 6. On-Resistance Variation with Temperature



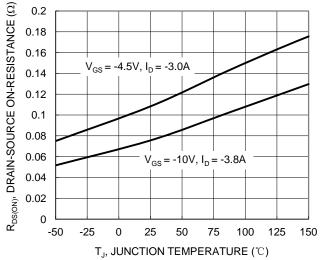
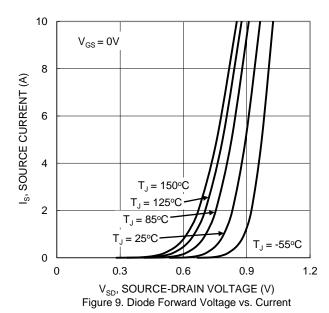
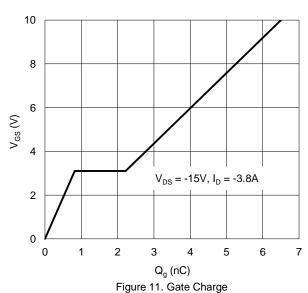


Figure 7. On-Resistance Variation with Temperature





2 $V_{GS(TH)}, \ GATE\ THRESHOLD\ VOLTAGE\ (V)$ $I_D = -1mA$ 1.5 $I_{D} = -250 \mu A$ 1 0.5 -50 -25 25 50 75 100 125 150 T_J , JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature

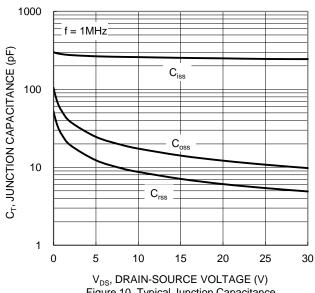


Figure 10. Typical Junction Capacitance

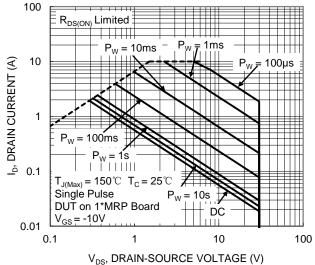


Figure 12. SOA, Safe Operation Area

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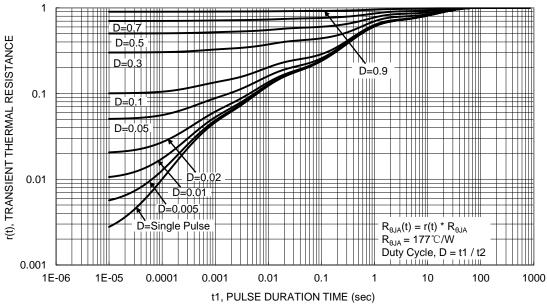


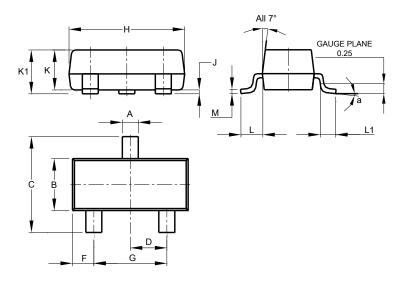
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

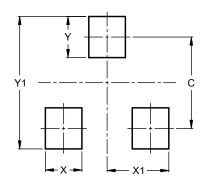


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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